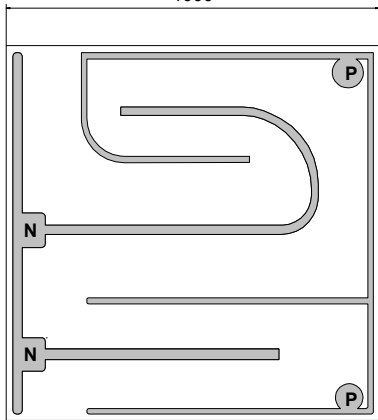


Radiation	Type	Technology	Electrodes
Blue	Standard	InGaN/Al ₂ O ₃	Both on top side

	typ. dimensions (± 25) μm
	typ. thickness 90 (± 10) μm <u>contact metalization</u> gold alloy, 1.5 μm <u>backside metalization</u> aluminium alloy, 1.0 μm

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 20 mA	V _F		2.7	3.0	V
Forward voltage ¹⁾	I _F = 350 mA	V _F		3.24	3.7	V
Reverse voltage	I _R = 10 μA	V _R	5			V
Radiant power	I _F = 20 mA	Φ_e	8.8	11.5		mW
Radiant power ^{1,2)}	I _F = 350 mA	Φ_e		150		mW
Luminous intensity ¹⁾	I _F = 350 mA	I _V	6000	6500		mcd
Peak wavelength	I _F = 350 mA	λ_p		467		nm
Dominant wavelength	I _F = 350 mA	λ_p	465	470	475	nm
Spectral bandwidth at 50%	I _F = 350 mA	$\Delta\lambda_{0.5}$		35		nm
Switching time	I _F = 20 mA	t _r , t _f		60		ns

¹⁾ Measured on bare chip on TO-18 header

²⁾ information only

Labeling

Type	Lot N°	Φ_e (typ) [mW]	V _F (typ) [V]	Quantity
ELC-470-31-1				

Packing: Chips on adhesive film with wire-bond side on top

Note: All measurements carried out with *EPIGAP* equipment